

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VLB10-12S is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|-------------------------------|
| I_C | 2.0 A |
| V_{CB0} | 36 V |
| V_{CEO} | 18 V |
| V_{CES} | 36 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 20 W @ T _C = 25 °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 5.0 °C/W |

PACKAGE STYLE .380 4L STUD

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .980 / 24.89 | |
| C | .370 / 9.40 | .385 / 9.78 |
| D | .004 / 0.10 | .007 / 0.18 |
| E | .320 / 8.13 | .330 / 8.38 |
| F | .100 / 2.54 | .130 / 3.30 |
| G | .450 / 11.43 | .490 / 12.45 |
| H | .090 / 2.29 | .100 / 2.54 |
| I | .155 / 3.94 | .175 / 4.45 |
| J | | .750 / 19.05 |

ORDER CODE: ASI10734

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|----------------------------------------------|-----------------------------------------------------------------------|---------|---------|---------|---------|
| BV_{CEO} | I _C = 15 mA | 18 | | | V |
| BV_{CES} | I _C = 50 mA | 36 | | | V |
| BV_{EBO} | I _E = 2.5 mA | 4.0 | | | V |
| I_{CB0} | V _{CB} = 12.5 V | | | 1.0 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 250 mA | 5.0 | | 200 | --- |
| C_{OB} | V _{CB} = 12.5 V f = 1.0 MHz | | | 65 | pF |
| P_G η_C | V _{CC} = 12.5 V P _{OUT} = 10 W f = 50 MHz | 10 | 60 | | dB % |